

ABSTRACT

Disclosed is a granular resin composition for encapsulating a semiconductor used for a semiconductor device obtained by encapsulating a semiconductor element by compression molding, satisfying the following requirements (a) to (c) on condition that ion viscosity is measured with a dielectric analyzer under a measurement temperature of 175°C and a measurement frequency of 100 Hz:

(a) the time from the initiation of the measurement until a decrease of the ion viscosity to the lowest ion viscosity is 20 seconds or shorter;

(b) the lowest ion viscosity value is not more than 6.5; and

(c) the time interval between the time from the initiation of the measurement until a decrease of the ion viscosity to the lowest ion viscosity and the time from the initiation of the measurement until the ion viscosity reaching 90% of an ion viscosity value measured at 300 seconds is 10 seconds or longer.